imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

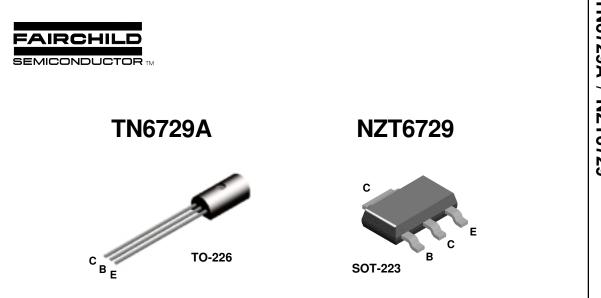
We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 800 mA. Sourced from Process 79.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		TN6729A	*NZT6729		
P _D	Total Device Dissipation	1.0	1.0	W	
	Derate above 25°C	8.0	8.0	mW/∘C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	125	°C/W	

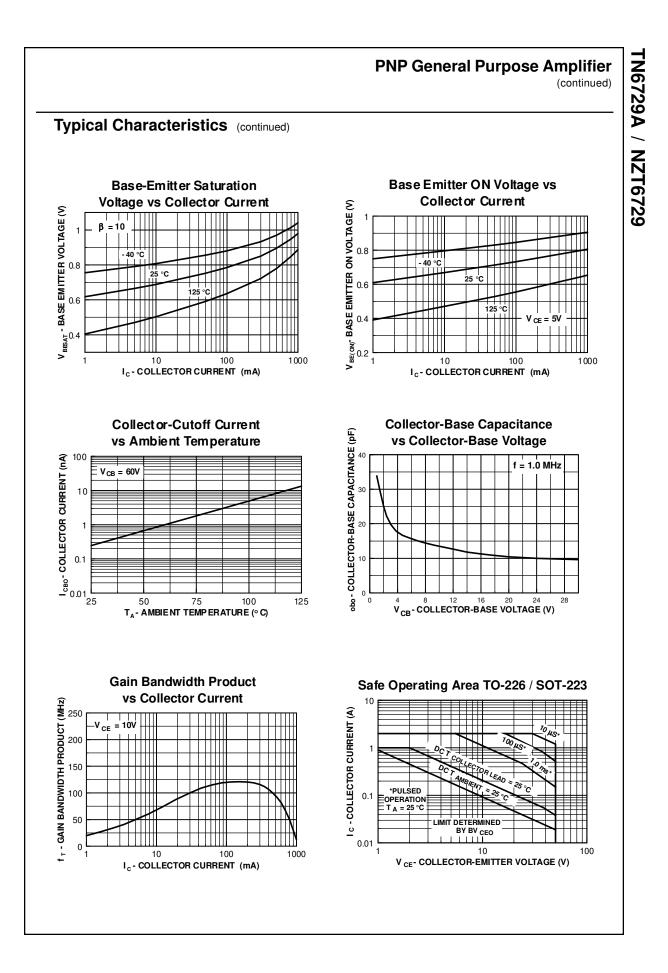
*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

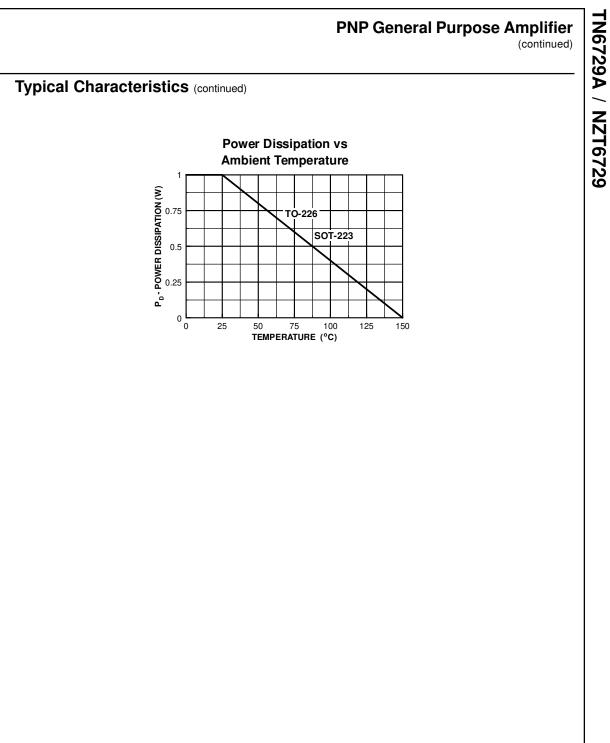
© 1997 Fairchild Semiconductor Corporation

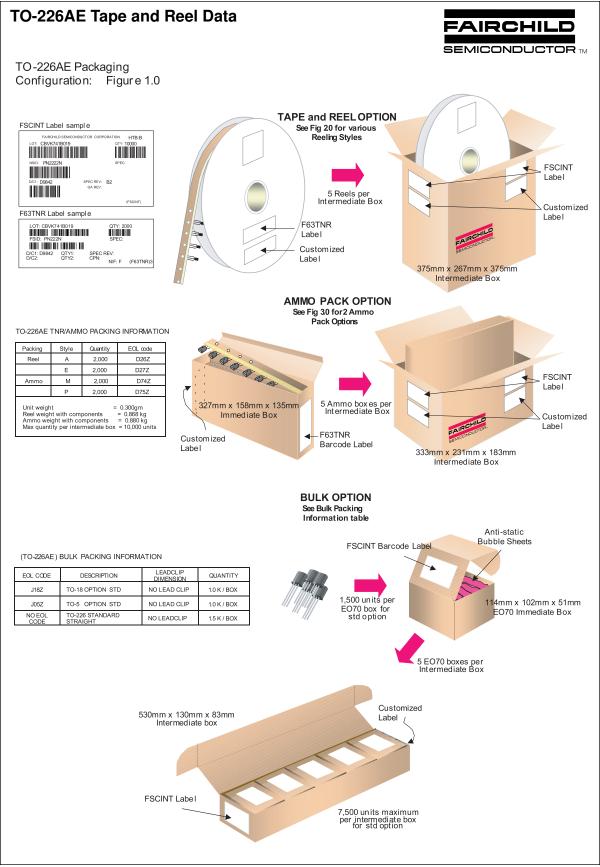
PNP General Purpose Amplifier

V(BR)CEO (V(BR)CBO (V(BR)EBO (IcBO (IeBO (ON CHARAC (h _{FE} I	ACTERISTICS Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$\begin{split} I_{C} &= 1.0 \text{ mA}, I_{B} = 0 \\ I_{C} &= 100 \ \mu\text{A}, I_{E} = 0 \\ I_{E} &= 1.0 \ \text{mA}, I_{C} = 0 \\ V_{CB} &= 60 \ \text{V}, I_{E} = 0 \\ V_{EB} &= 5.0 \ \text{V}, I_{C} = 0 \end{split}$	80 80 5.0		V
V(BR)CEO (V(BR)CBO (V(BR)EBO (IcBO (IeBO (ON CHARAC (h _{FE} I	Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$\begin{split} I_{C} &= 100 \; \mu A, \; I_{E} = 0 \\ I_{E} &= 1.0 \; m A, \; I_{C} = 0 \\ V_{CB} &= 60 \; V, \; I_{E} = 0 \end{split}$	80		
V(BR)CBO (V(BR)CBO I IcBO I IcBO (NCHARA(NCHARA(h _{FE} I	Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$\begin{split} I_{C} &= 100 \; \mu A, \; I_{E} = 0 \\ I_{E} &= 1.0 \; m A, \; I_{C} = 0 \\ V_{CB} &= 60 \; V, \; I_{E} = 0 \end{split}$	80		V
V _{(BR)EBO} I I _{CBO} (I _{EBO} I ON CHARA(h _{FE} I	Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	$I_{E} = 1.0 \text{ mA}, I_{C} = 0$ $V_{CB} = 60 \text{ V}, I_{E} = 0$			
CBO (EBO I DN CHARAG	Collector-Cutoff Current Emitter-Cutoff Current	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$			V
DN CHARAC	Emitter-Cutoff Current			0.1	μA
ı _{fe} I	CTERISTICS*			10	μA
ı _{fe} I					
	DC Current Gain	I _C = 50 mA, V _{CE} = 1.0 V	80		
		I _C = 250 mA, V _{CE} = 1.0 V	50	250	
		$I_{\rm C} = 500 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	20	0.5	V
/ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 250 \text{ mA}, I_{\rm B} = 10 \text{ mA}$ $I_{\rm C} = 250 \text{ mA}, I_{\rm B} = 25 \text{ mA}$		0.5 0.35	v
/ _{BE(on)}	Base-Emitter On Voltage	$I_{C} = 250 \text{ mA}, I_{B} = 25 \text{ mA}$ $I_{C} = 250 \text{ mA}, V_{CE} = 1.0 \text{ V}$		1.2	V
*Pulse Test: Pulse	Collector-Base Capacitance a Width \leq 300 µs, Duty Cycle \leq 1.0% s (V) and currents (A) are negative polarity for PNP	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF
Тур	Characteristics pical Pulsed Current Gain vs Collector Current	Collector- ᢓᢩ Voltage vs			
200 C					
P ² − 40 000 000 000 000 000 000 000 000 00	V _{CE} = 1.0	\vec{v} \vec{h} $\beta = 10$			
H 150 125				25 °C	
1 25 °		6 0.1			
	<u>;</u>	E E		125 °C	
	Ĭ				
50 - 40°		V Voltage vs γ $\beta = 10$ $\beta = 10$			$+ \square$

TN6729A / NZT6729

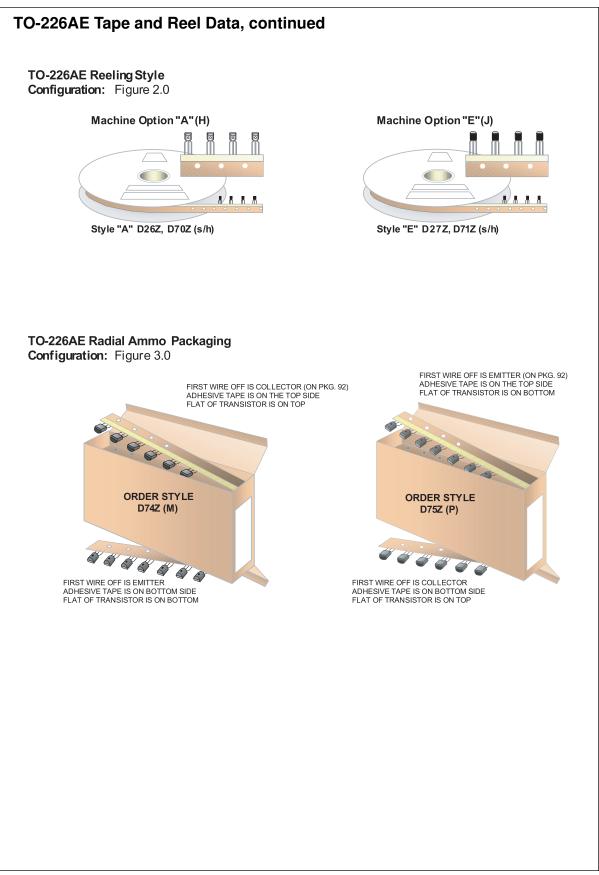


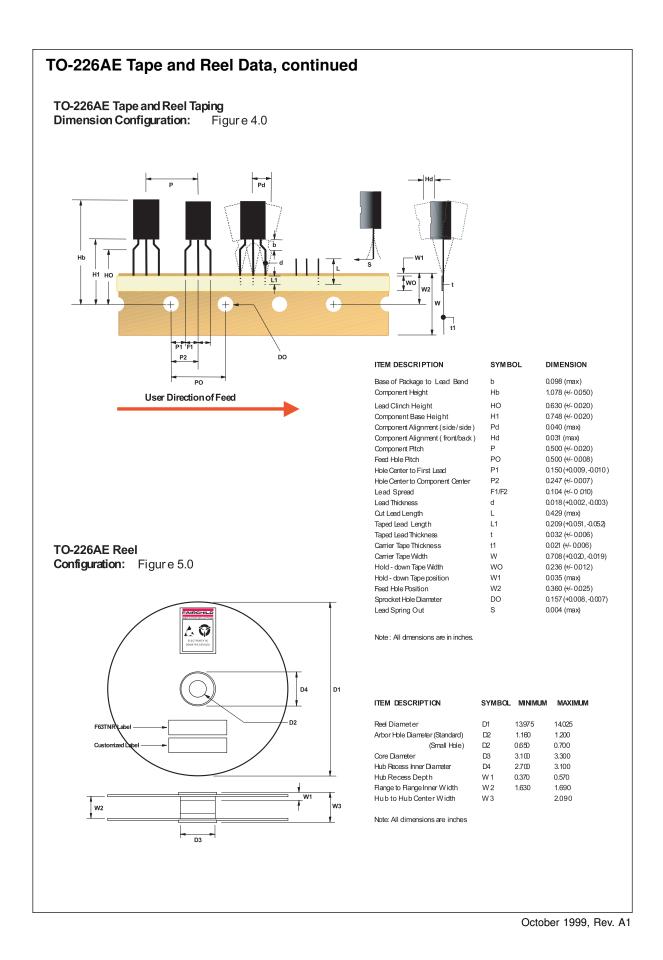


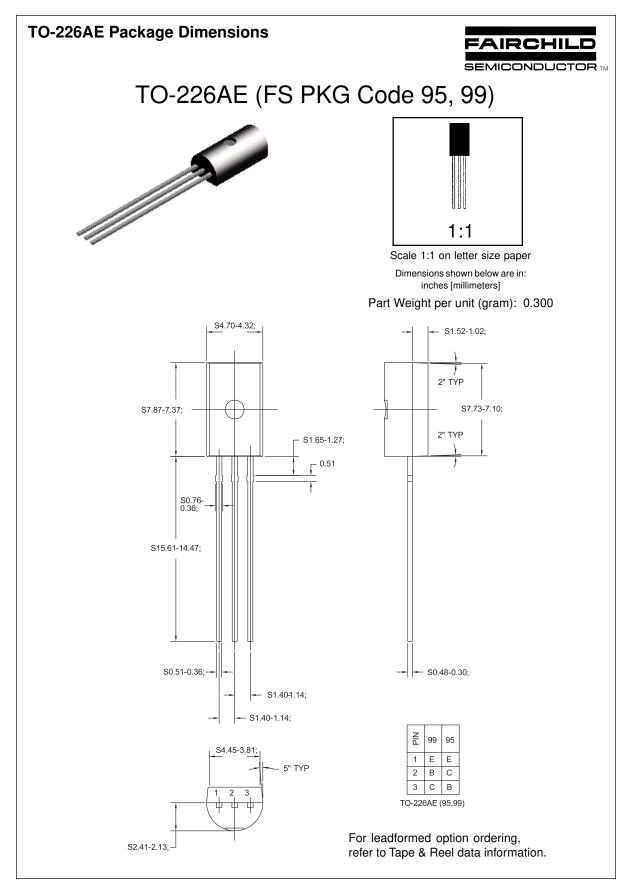


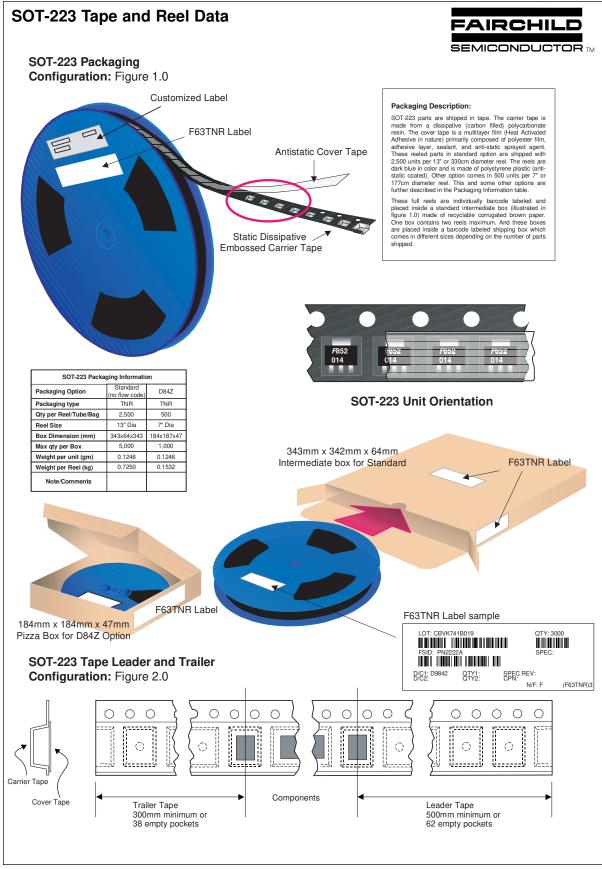
©2000 Fairchild Semiconductor International

October 1999, Rev. A1



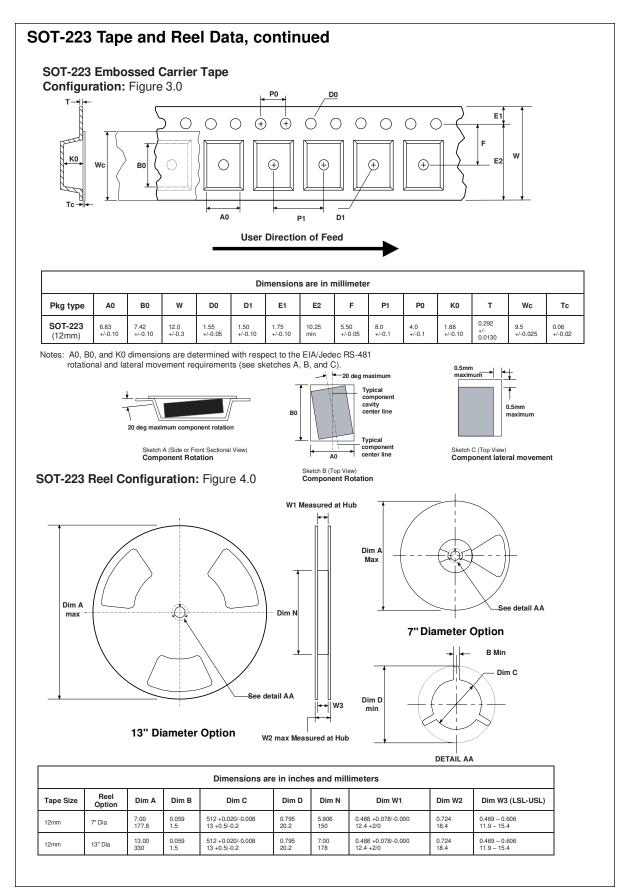


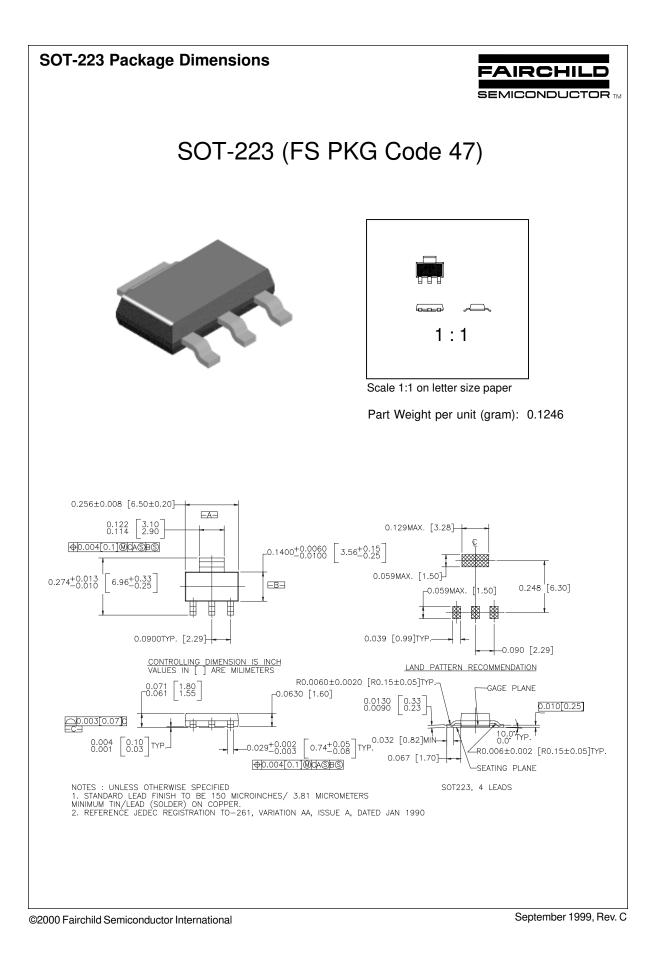




©2000 Fairchild Semiconductor International

September 1999, Rev. B





TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™ Bottomless™ CoolFET™ CROSSVOLT™ DOME™ E²CMOS[™] EnSigna™ FACT™ FACT Quiet Series[™] FAST[®]

FASTr™ GlobalOptoisolator[™] GTO™ HiSeC™ ISOPLANAR™ MICROWIRE™ OPTOLOGIC™ **OPTOPLANAR™** PACMAN™ **POP™**

- PowerTrench[®] QFET™ QS™ QT Optoelectronics[™] Quiet Series[™] SILENT SWITCHER® SMART START™ SuperSOT[™]-3 SuperSOT[™]-6 SuperSOT[™]-8
- SyncFET™ TinyLogic™ UHC™ **VCX™**

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.